



RF Power Field Effect Transistors

N-Channel Enhancement-Mode Lateral MOSFET

Designed for broadband commercial and industrial applications with frequencies from 865 to 895 MHz. The high gain and broadband performance of this device makes it ideal for large-signal, common source amplifier applications in 26 volt base station equipment.

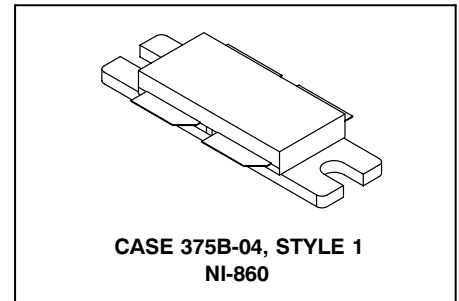
- Typical CDMA Performance @ 880 MHz, 26 Volts, $I_{DQ} = 1000$ mA
 IS-95 CDMA (Pilot, Sync, Paging, Traffic Codes 8 Through 13)
 Output Power — 26 Watts
 Power Gain — 16 dB
 Efficiency — 26%
 Adjacent Channel Power —
 750 kHz: -45 dBc in 30 kHz BW
 1.98 MHz: -60 dBc in 30 kHz BW
- Capable of Handling 10:1 VSWR, @ 26 Vdc, 880 MHz, 120 Watts CW Output Power

Features

- Characterized with Series Equivalent Large-Signal Impedance Parameters
- Integrated ESD Protection
- Designed for Maximum Gain and Insertion Phase Flatness
- Excellent Thermal Stability
- Available with Low Gold Plating Thickness on Leads. L Suffix Indicates 40 μ m Nominal.
- RoHS Compliant
- In Tape and Reel. R3 Suffix = 250 Units per 56 mm, 13 inch Reel.



**880 MHz, 120 W, 26 V
 LATERAL N-CHANNEL
 RF POWER MOSFET**



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Table 1. Maximum Ratings

Rating	Symbol	Value	Unit
Drain-Source Voltage	V_{DSS}	- 0.5, +65	Vdc
Gate-Source Voltage	V_{GS}	- 0.5, +15	Vdc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above 25°C	P_D	250 1.43	W W/°C
Storage Temperature Range	T_{stg}	- 65 to +150	°C
Case Operating Temperature	T_C	150	°C
Operating Junction Temperature	T_J	200	°C

Table 2. Thermal Characteristics

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction to Case	$R_{\theta JC}$	0.45	°C/W

Table 3. ESD Protection Characteristics

Test Conditions	Class
Human Body Model	1 (Minimum)
Machine Model	M1 (Minimum)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Typ	Max	Unit
Off Characteristics ⁽¹⁾					
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 65\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	10	μAdc
Zero Gate Voltage Drain Leakage Current ($V_{DS} = 26\text{ Vdc}$, $V_{GS} = 0\text{ Vdc}$)	I_{DSS}	—	—	1	μAdc
Gate-Source Leakage Current ($V_{GS} = 5\text{ Vdc}$, $V_{DS} = 0\text{ Vdc}$)	I_{GSS}	—	—	1	μAdc
On Characteristics					
Gate Threshold Voltage ⁽¹⁾ ($V_{DS} = 10\text{ Vdc}$, $I_D = 200\ \mu\text{Adc}$)	$V_{GS(th)}$	2	3	4	Vdc
Gate Quiescent Voltage ⁽²⁾ ($V_{DS} = 26\text{ Vdc}$, $I_D = 1000\text{ mAdc}$)	$V_{GS(Q)}$	—	3.8	—	Vdc
Drain-Source On-Voltage ⁽¹⁾ ($V_{GS} = 10\text{ Vdc}$, $I_D = 1.3\text{ Adc}$)	$V_{DS(on)}$	—	0.17	0.4	Vdc
Dynamic Characteristics ^(1,3)					
Output Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{OSS}	—	50	—	pF
Reverse Transfer Capacitance ($V_{DS} = 26\text{ Vdc} \pm 30\text{ mV(rms)ac}$ @ 1 MHz, $V_{GS} = 0\text{ Vdc}$)	C_{RSS}	—	2	—	pF

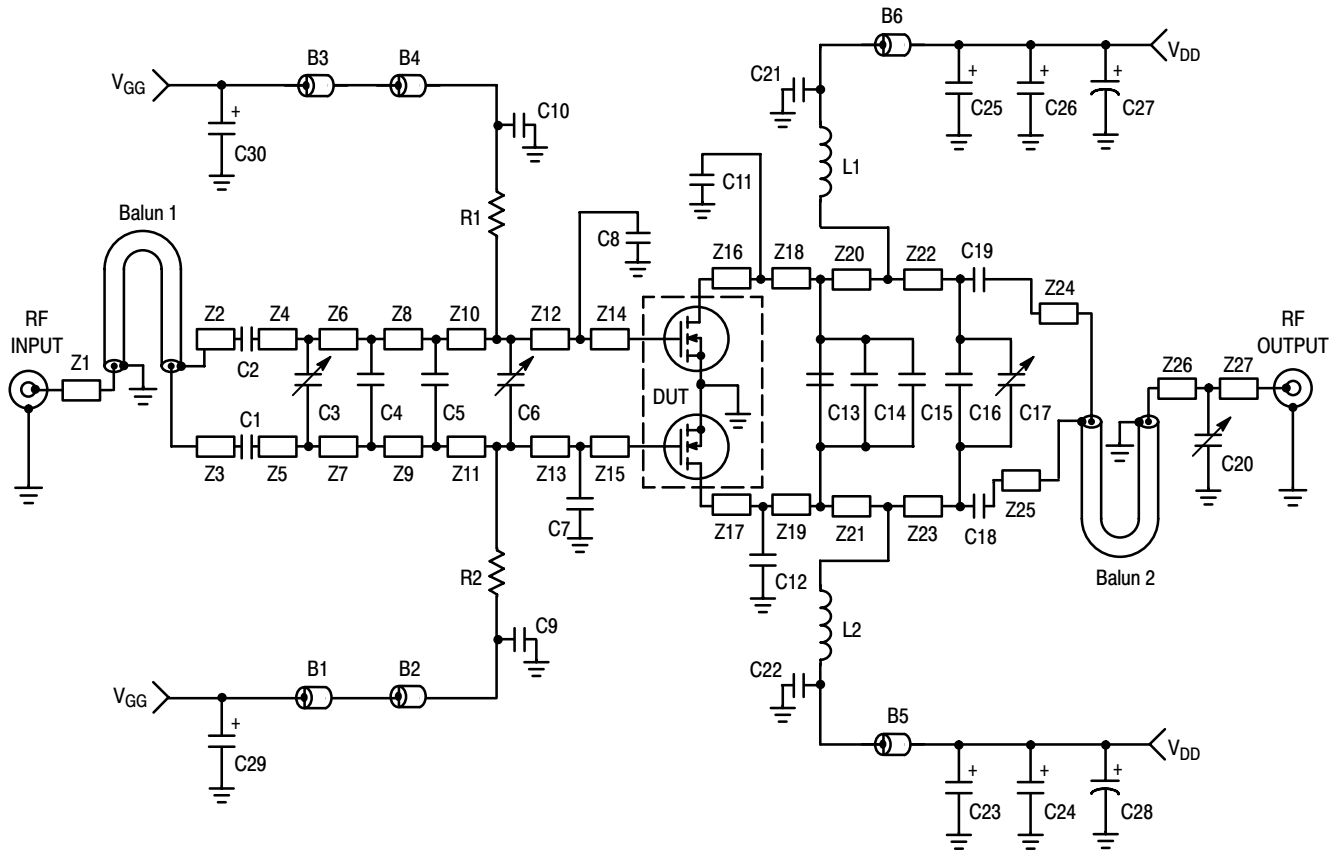
1. Each side of device measured separately.
2. Measurement made with device in push-pull configuration.
3. Part internally input matched.

(continued)

Table 4. Electrical Characteristics ($T_C = 25^\circ\text{C}$ unless otherwise noted) (continued)

Characteristic	Symbol	Min	Typ	Max	Unit
Functional Tests ⁽¹⁾ (In Freescale Test Fixture, 50 ohm system)					
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	G_{ps}	15	16.5	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	η	36	39	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	IMD	—	-31	-28	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$, $f_2 = 880.1\text{ MHz}$)	IRL	—	-16	-9	dB
Two-Tone Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 895.0\text{ MHz}$, $f_2 = 895.1\text{ MHz}$)	G_{ps}	—	16.5	—	dB
Two-Tone Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 895.0\text{ MHz}$, $f_2 = 895.1\text{ MHz}$)	η	—	40.5	—	%
3rd Order Intermodulation Distortion ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 895.0\text{ MHz}$, $f_2 = 895.1\text{ MHz}$)	IMD	—	-30	—	dBc
Input Return Loss ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W PEP}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 895.0\text{ MHz}$, $f_2 = 895.1\text{ MHz}$)	IRL	—	-13	—	dB
Power Output, 1 dB Compression Point ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W CW}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	P_{1dB}	—	120	—	W
Common-Source Amplifier Power Gain ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W CW}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	G_{ps}	—	16	—	dB
Drain Efficiency ($V_{DD} = 26\text{ Vdc}$, $P_{out} = 120\text{ W CW}$, $I_{DQ} = 1000\text{ mA}$, $f_1 = 880.0\text{ MHz}$)	η	—	51	—	%

1. Measurement made with device in push-pull configuration.

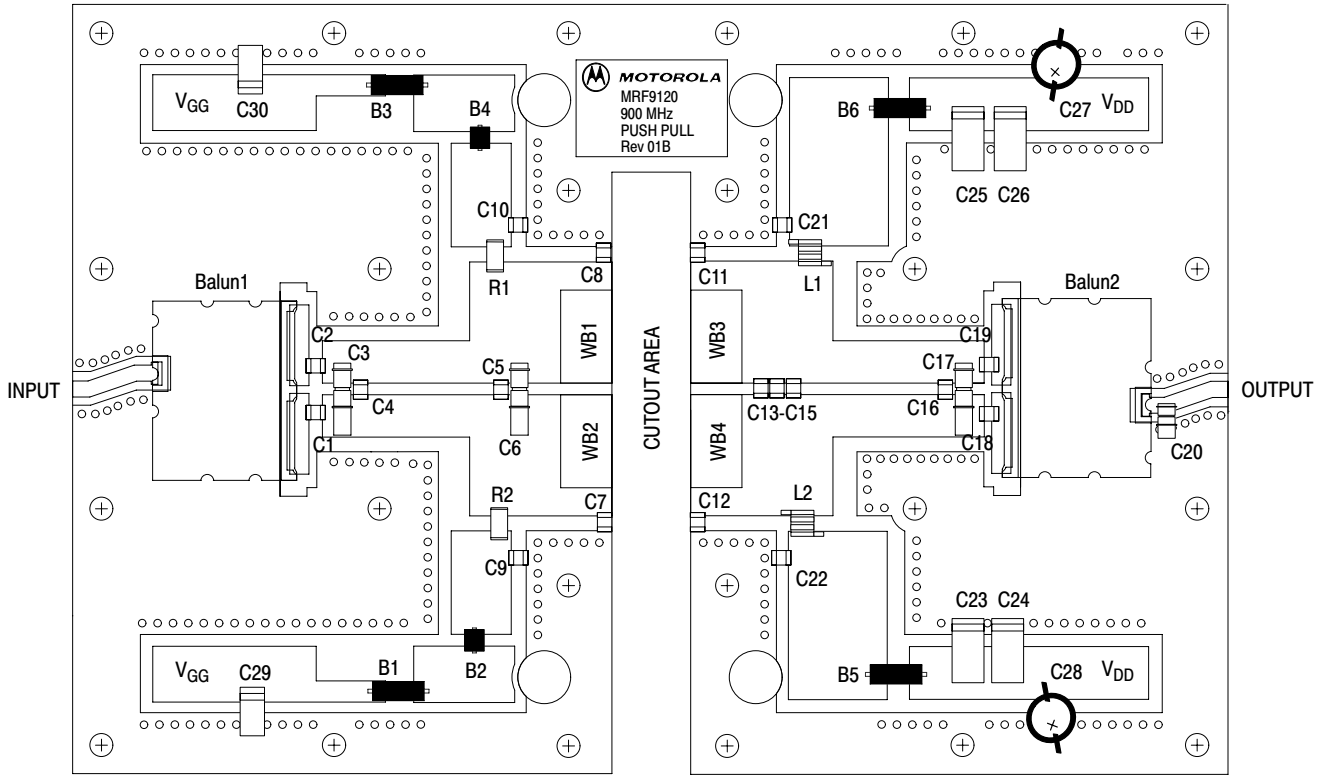


Z1	0.420" x 0.080" Microstrip	Z14, Z15	0.040" x 0.630" Microstrip
Z2, Z3	0.090" x 0.420" Microstrip	Z16, Z17	0.040" x 0.630" Microstrip
Z4, Z5	0.125" x 0.220" Microstrip	Z18, Z19	0.330" x 0.630" Microstrip
Z6, Z7	0.095" x 0.220" Microstrip	Z20, Z21	0.450" x 0.630" Microstrip
Z8, Z9	0.600" x 0.220" Microstrip	Z22, Z23	0.750" x 0.220" Microstrip
Z10, Z11	0.200" x 0.630" Microstrip	Z24, Z25	0.115" x 0.420" Microstrip
Z12, Z13	0.500" x 0.630" Microstrip	Z26	0.130" x 0.080" Microstrip
		Z27	0.350" x 0.080" Microstrip

Figure 1. 880 MHz Broadband Test Circuit Schematic

Table 5. 880 MHz Broadband Test Circuit Component Designations and Values

Part	Description	Part Number	Manufacturer
B1, B3, B5, B6	Long Ferrite Beads, Surface Mount	95F787	Newark
B2, B4	Short Ferrite Beads, Surface Mount	95F786	Newark
C1, C2	68 pF Chip Capacitors	100B680JP500X	ATC
C3, C6	0.8 - 8.0 pF Variable Capacitors	44F3360	Newark
C4	7.5 pF Chip Capacitor	100B7R5JP150X	ATC
C5	3.3 pF Chip Capacitor	100B3R3CP150X	ATC
C7, C8	11 pF Chip Capacitors	100B110BCA500X	ATC
C9, C10, C21, C22	51 pF Chip Capacitors	100B510JP500X	ATC
C11, C12	6.2 pF Chip Capacitors	100B6R2BCA150X	ATC
C13	4.7 pF Chip Capacitor	100B4R7BCA150X	ATC
C14	5.1 pF Chip Capacitor	100B5R1BCA150X	ATC
C15	3.0 pF Chip Capacitor	100B2R7BCA150X	ATC
C16	2.7 pF Chip Capacitor	100B3R0BCA150X	ATC
C17	0.6 - 4.5 pF Variable Capacitor	44F3358	Newark
C18, C19	47 pF Chip Capacitors	100B470JP500X	ATC
C20	0.4 - 2.5 pF Variable Capacitor	44F3367	Newark
C29, C30	10 μ F, 35 V Tantalum Chip Capacitors	93F2975	Newark
C23, C24, C25, C26	22 μ F, 35 V Tantalum Chip Capacitors	92F1853	Newark
C27, C28	220 μ F, 50 V Electrolytic Capacitors	14F185	Newark
Balun 1, Balun 2	Xinger Surface Mount Balun Transformers	3A412	Anaren
L1, L2	12.5 nH Mini Spring Inductors	A04T-5	Coilcraft
R1, R2	510 Ω , 1/4 W Chip Resistors		
WB1, WB2, WB3, WB4	10 mil Brass Wear Blocks		
Board Material	30 mil Glass Teflon [®] , $\epsilon_r = 2.55$ Copper Clad, 2 oz Cu	900 MHz Push-Pull Rev 01B	CMR
PCB	Etched Circuit Board	900 MHz Push-Pull Rev 01B	CMR



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. 865-895 MHz Broadband Test Circuit Component Layout

TYPICAL CHARACTERISTICS

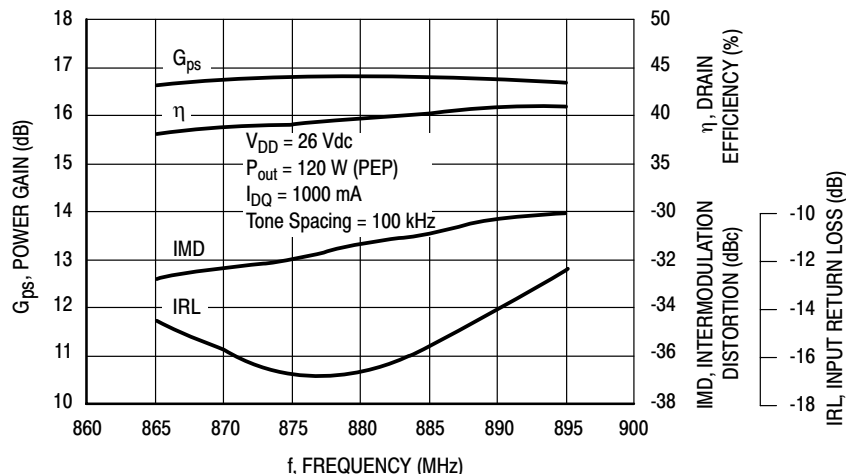


Figure 3. Class AB Broadband Circuit Performance

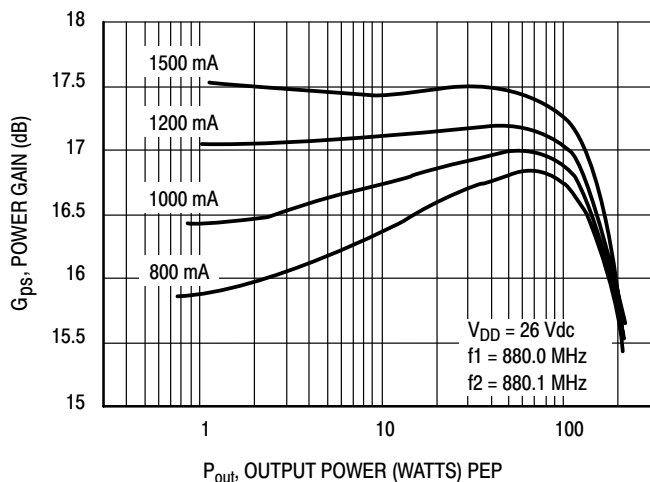


Figure 4. Power Gain versus Output Power

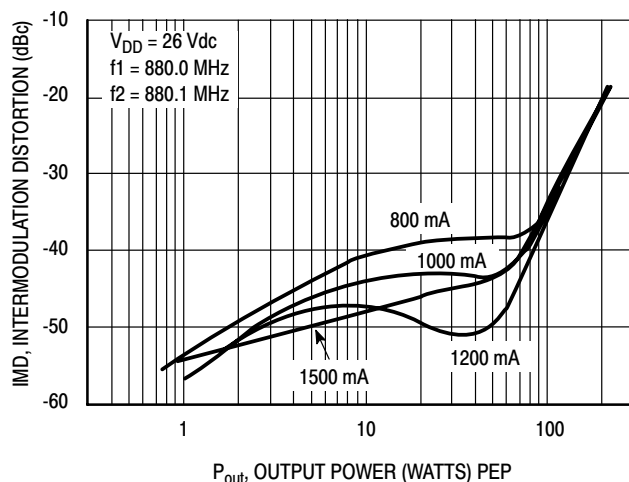


Figure 5. Intermodulation Distortion versus Output Power

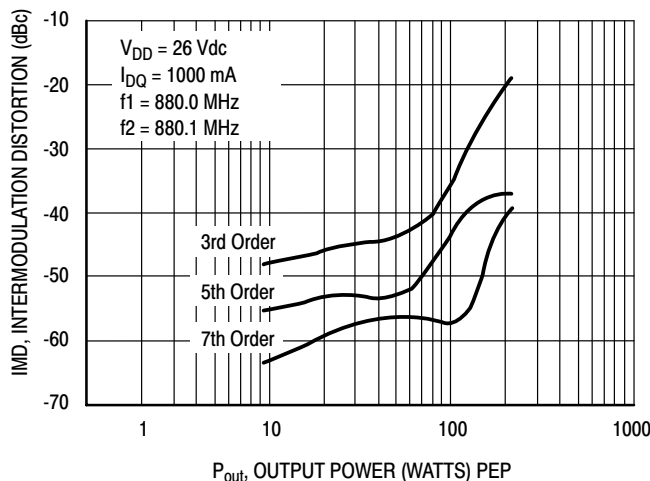


Figure 6. Intermodulation Distortion Products versus Output Power

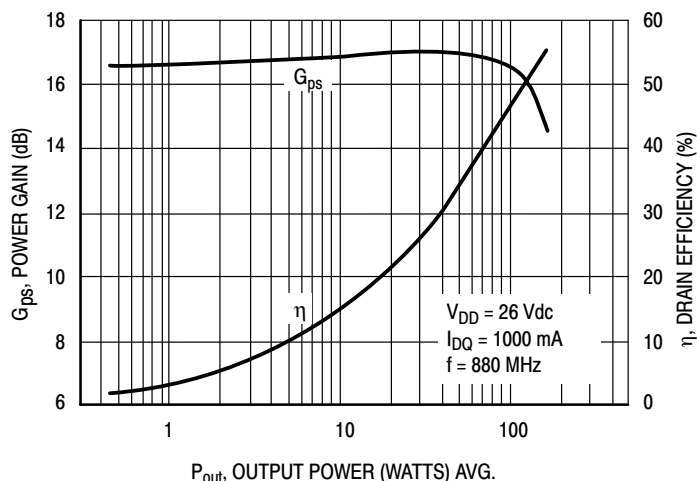


Figure 7. Power Gain and Efficiency versus Output Power

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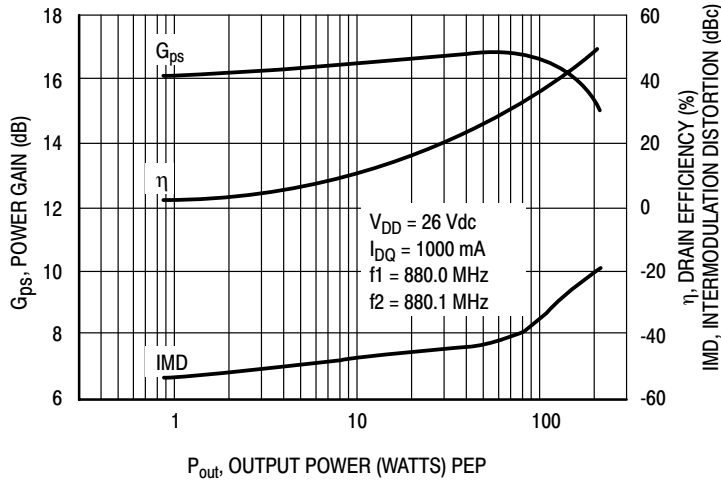


Figure 8. Power Gain, Efficiency and IMD versus Output Power

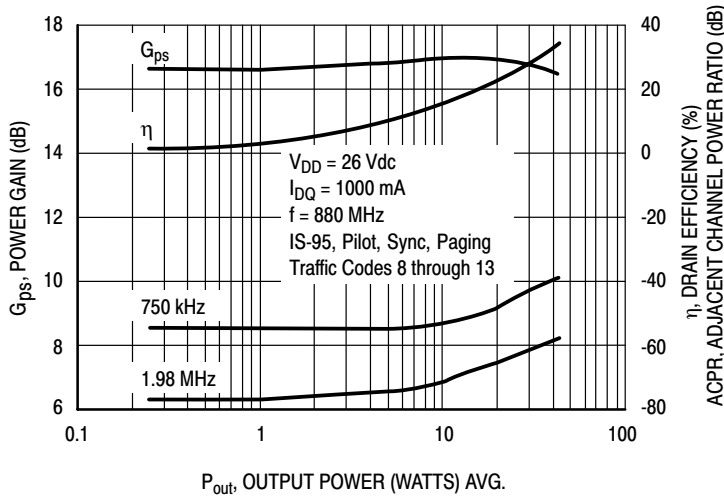
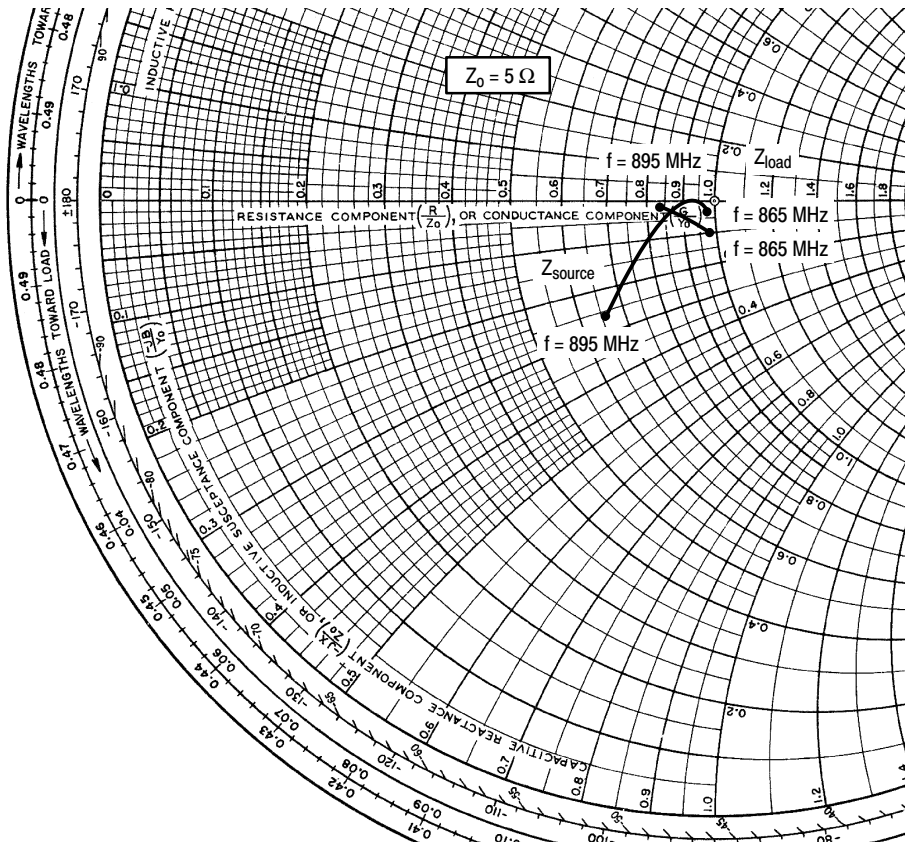


Figure 9. Power Gain, Efficiency and ACPR versus Output Power



$V_{DD} = 26\text{ V}$, $I_{DQ} = 1000\text{ mA}$, $P_{out} = 120\text{ W PEP}$

f MHz	Z_{source} Ω	Z_{load} Ω
865	$4.89 - j0.2$	$4.9 - j0.5$
880	$4.54 + j0.07$	$4.6 - j0.32$
895	$3.29 - j1.3$	$4.2 - j0.04$

Z_{source} = Test circuit impedance as measured from gate to gate, balanced configuration.

Z_{load} = Test circuit impedance as measured from drain to drain, balanced configuration.

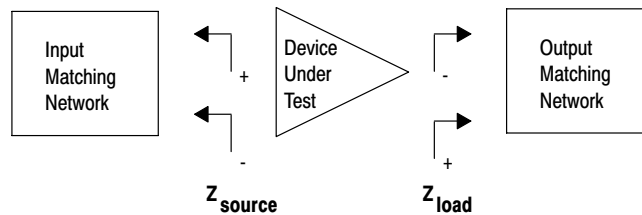
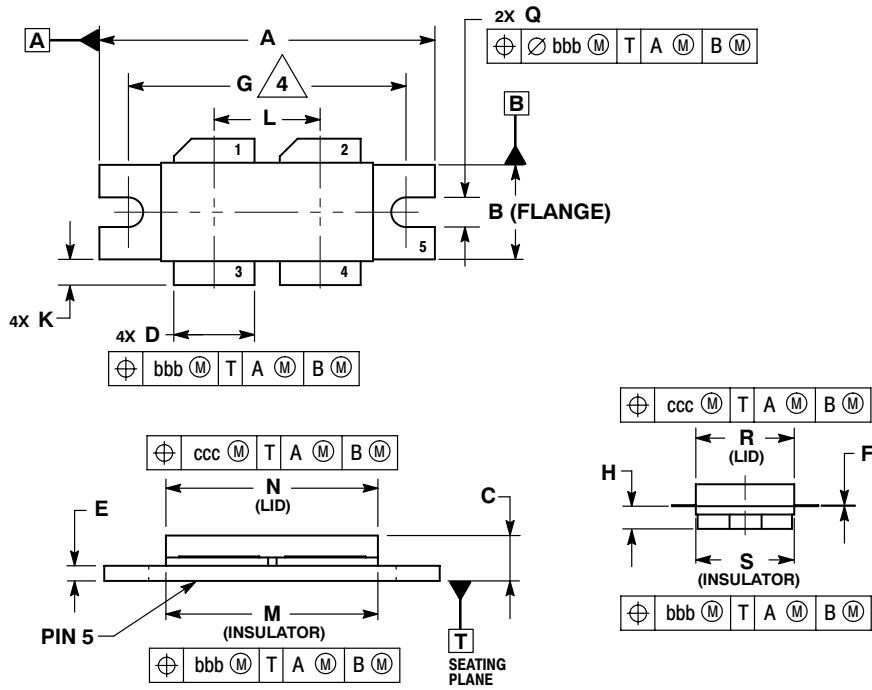


Figure 10. Series Equivalent Source and Load Impedance

PACKAGE DIMENSIONS



- NOTES:
1. INTERPRET DIMENSIONS AND TOLERANCES PER ASME Y14.5M-1994.
 2. CONTROLLING DIMENSION: INCH.
 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.
 4. RECOMMENDED BOLT CENTER DIMENSION OF 1.140 (28.96) BASED ON M3 SCREW.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	1.335	1.345	33.91	34.16
B	0.380	0.390	9.65	9.91
C	0.180	0.224	4.57	5.69
D	0.325	0.335	8.26	8.51
E	0.060	0.070	1.52	1.78
F	0.004	0.006	0.10	0.15
G	1.100 BSC		27.94 BSC	
H	0.097	0.107	2.46	2.72
K	0.085	0.115	2.16	2.92
L	0.425 BSC		10.80 BSC	
M	0.852	0.868	21.64	22.05
N	0.851	0.869	21.62	22.07
Q	0.118	0.138	3.00	3.51
R	0.395	0.405	10.03	10.29
S	0.394	0.406	10.01	10.31
bbb	0.010 REF		0.25 REF	
ccc	0.015 REF		0.38 REF	

- STYLE 1:
1. DRAIN
 2. DRAIN
 3. GATE
 4. GATE
 5. SOURCE

**CASE 375B-04
ISSUE F
NI-860**

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
10	Dec. 2009	<ul style="list-style-type: none">Data sheet archived. Part no longer manufactured.

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